

Single N-Channel Power MOSFET 80V, 335A, 1.1mΩ, PQFN 8x8

Manufacturers	ON Semiconductor, LLC
Package/Case	DFNW-8
Product Type	
RoHS	
Lifecycle	



Images are for reference only

Please submit RFQ for NTMTS1D2N08H or [Email to us: sales@ovaga.com](mailto:sales@ovaga.com) We will contact you in 12 hours.

[RFQ](#)

General Description

This N-Channel T8 80V MV MOSFET is produced using ON Semiconductor's advanced Power Trench process that incorporates Shielded Gate technology. This process has been optimized to minimize on-state resistance and yet maintain superior switching performance.

Features

- Very Low RDS(on), Shielded Gate Trench Technology
- Minimize conduction losses
- Low Profile PQFN 8x8 package
- High peak current and low parasitic inductance
- Maximum junction temperature of 175C
- Offers a wider design margin for thermally challenged applications
- RoHS Compliant

Application

ONSEMI

Related Products



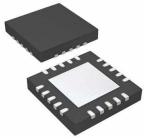
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QFN32 4x4, 0.4P



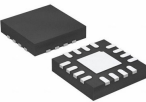
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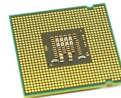
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